

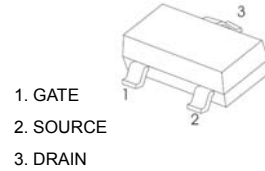


# SOT-23 Plastic-Encapsulate Transistors

## 1H05 N-Channel MOSFET

| $V_{(BR)DSS}$ | $R_{DS(on)MAX}$ | $I_D$ |
|---------------|-----------------|-------|
| 100V          | 234mΩ@10V       | 5A    |
|               | 247mΩ@6V        |       |
|               | 258mΩ@4.5V      |       |

SOT-23



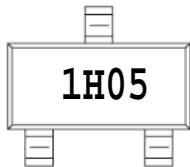
### FEATURE

- TrenchFET Power MOSFET
- Low  $R_{DS(ON)}$
- Surface Mount Package

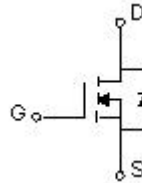
### APPLICATION

- DC/DC Converters
- Load Switch
- LED Backlighting in LCD TVs

### MARKING



### Equivalent Circuit



### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^{\circ}C$ unless otherwise noted)

| Parameter  | Symbol          | Value    | Unit          |
|--|-----------------|----------|---------------|
| Drain-Source Voltage   | $V_{DS}$        | 100      | V             |
| Gate-Source Voltage  | $V_{GS}$        | ±20      | V             |
| Continuous Drain Current   | $I_D$           | 5        | A             |
| Pulsed Drain Current   | $I_{DM}^*$      | 8        | A             |
| Thermal Resistance from Junction to Ambient                      | $R_{\theta JA}$ | 357      | $^{\circ}C/W$ |
| Junction Temperature   | $T_J$           | 150      | $^{\circ}C$   |
| Storage Temperature  | $T_{STG}$       | -55~+150 | $^{\circ}C$   |
| Lead Temperature for Soldering Purposes(1/8" from case for 10 s) | $T_L$           | 260      | $^{\circ}C$   |

\*Repetitive rating: Pulse width limited by junction temperature.

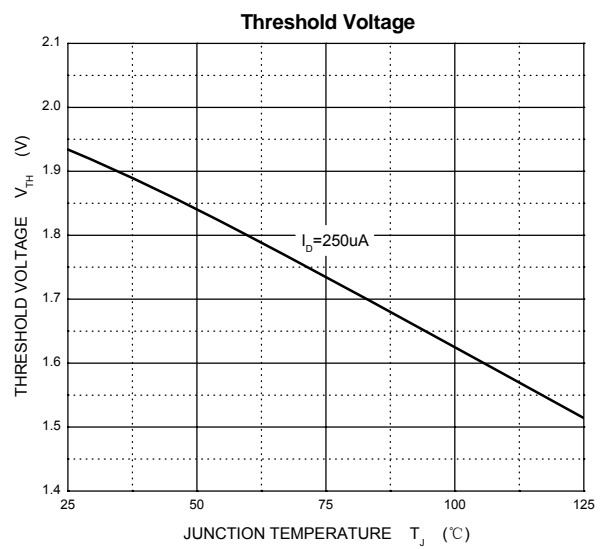
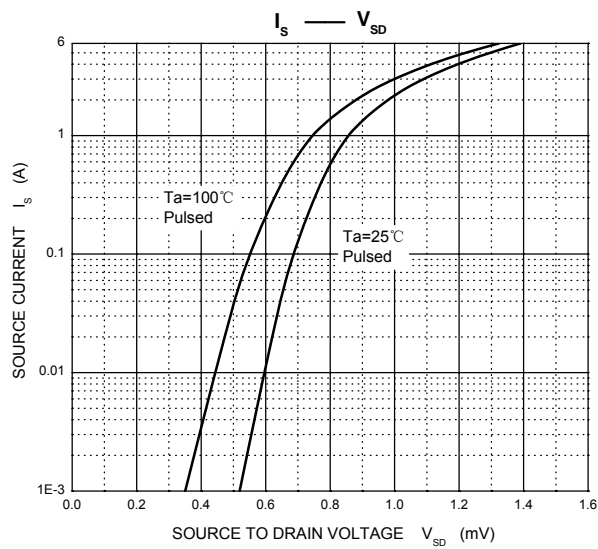
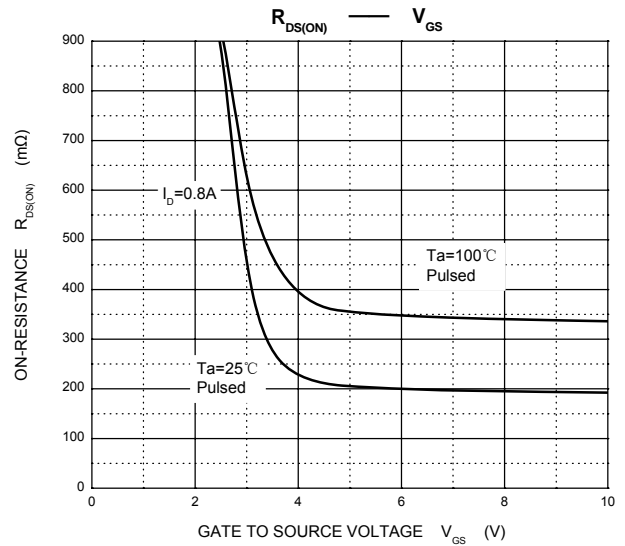
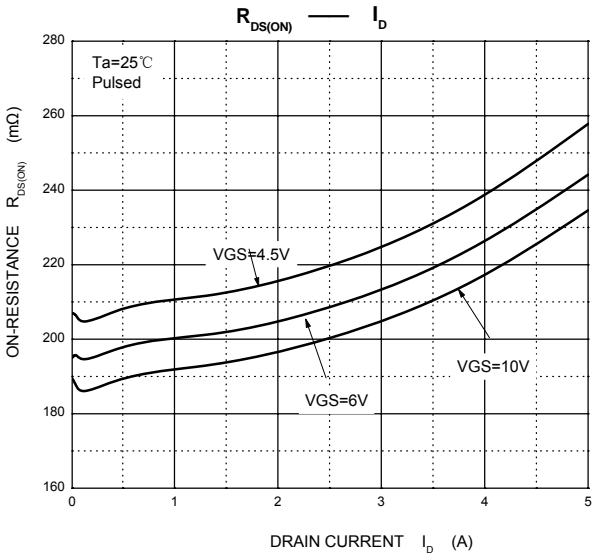
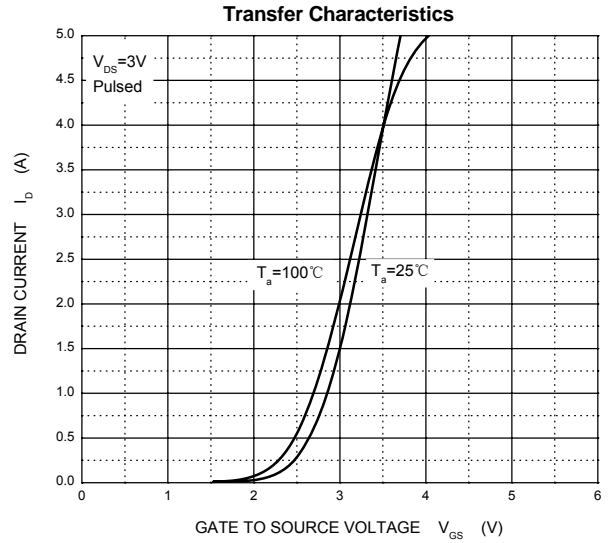
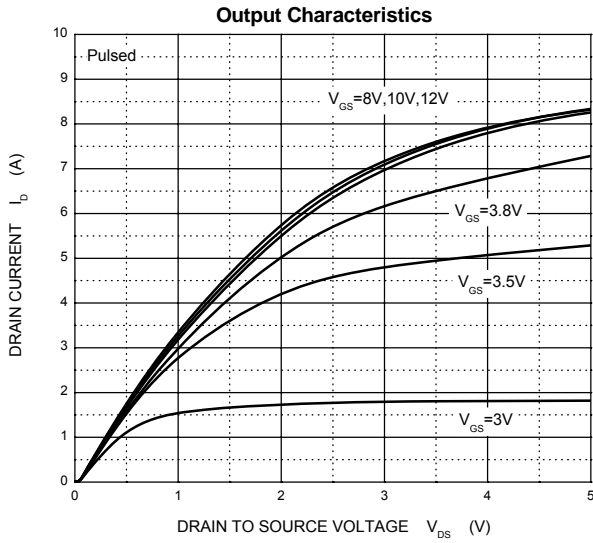
## MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$  unless otherwise specified

| Parameter                            | Symbol        | Test Condition  | Min | Typ  | Max       | Unit       |
|--------------------------------------|---------------|---|-----|------|-----------|------------|
| <b>STATIC PARAMETERS</b>             |               |   |     |      |           |            |
| Drain-source breakdown voltage       | $V_{(BR)DSS}$ | $V_{GS} = 0V, I_D = 250\mu A$   | 100 |      |           | V          |
| Zero gate voltage drain current      | $I_{DSS}$     | $V_{DS} = 100V, V_{GS} = 0V$  |     |      | 1         | $\mu A$    |
| Gate-body leakage current            | $I_{GSS}$     | $V_{GS} = \pm 20V, V_{DS} = 0V$   |     |      | $\pm 100$ | nA         |
| Gate threshold voltage(note 1)       | $V_{GS(th)}$  | $V_{DS} = V_{GS}, I_D = 250\mu A$   | 1.2 |      | 2.8       | V          |
| Drain-source on-resistance (note 1)  | $R_{DS(on)}$  | $V_{GS} = 10V, I_D = 5A$  |     |      | 234       | m $\Omega$ |
|                                      |               | $V_{GS} = 4.5V, I_D = 1A$   |     |      | 257       | m $\Omega$ |
|                                      |               | $V_{GS} = 10V, I_D = 1A$  |     |      | 220       | m $\Omega$ |
| Forward transconductance (note 1)    | $g_{FS}$      | $V_{DS} = 20V, I_D = 2.5A$  |     | 2    |           | S          |
| Diode forward voltage (note 1)       | $V_{SD}$      | $I_S = 1.3A, V_{GS} = 0V$   |     |      | 1.2       | V          |
| <b>DYNAMIC PARAMETERS (note2)</b>    |               |   |     |      |           |            |
| Input Capacitance                    | $C_{iss}$     | $V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$   |     | 190  |           | pF         |
| Output Capacitance                   | $C_{oss}$     |   |     | 22   |           | pF         |
| Reverse Transfer Capacitance         | $C_{rss}$     |   |     | 13   |           | pF         |
| Gate Resistance                      | $R_g$         | $F = 1MHz$  | 0.3 |      | 2.8       | $\Omega$   |
| <b>SWITCHING PARAMETERS (note 2)</b> |               |   |     |      |           |            |
| Turn-on delay time                   | $t_{d(on)}$   | $V_{DD} = 50V, V_{GEN} = 4.5V$<br>$R_L = 39\Omega, R_G = 1\Omega, I_D = 1.3A$ |     |      | 45        | ns         |
| Turn-on rise time                    | $t_r$         |   |     |      | 39        | ns         |
| Turn-off delay time                  | $t_{d(off)}$  |   |     |      | 26        | ns         |
| Turn-off fall time                   | $t_f$         |   |     |      | 20        | ns         |
| Total Gate Charge                    | $Q_g$         | $V_{DS} = 50V, V_{GS} = 4.5V, I_D = 1.6A$                                     |     |      | 5.8       | nC         |
| Gate-Source Charge                   | $Q_{gs}$      |   |     | 0.75 |           | nC         |
| Gate-Drain Charge                    | $Q_{gd}$      |   |     | 1.4  |           | nC         |

- Notes :**
1. Pulse Test : Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 0.5\%$ .
  2. Guaranteed by design, not subject to production testing.

# Typical Characteristics



## SOT-23 Package Outline Dimensions



| Symbol   | Dimensions In Millimeters |       | Dimensions In Inches |       |
|----------|---------------------------|-------|----------------------|-------|
|          | Min                       | Max   | Min                  | Max   |
| A        | 0.900                     | 1.150 | 0.035                | 0.045 |
| A1       | 0.000                     | 0.100 | 0.000                | 0.004 |
| A2       | 0.900                     | 1.050 | 0.035                | 0.041 |
| b        | 0.300                     | 0.500 | 0.012                | 0.020 |
| c        | 0.080                     | 0.150 | 0.003                | 0.006 |
| D        | 2.800                     | 3.000 | 0.110                | 0.118 |
| E        | 1.200                     | 1.400 | 0.047                | 0.055 |
| E1       | 2.250                     | 2.550 | 0.089                | 0.100 |
| e        | 0.950 TYP                 |       | 0.037 TYP            |       |
| e1       | 1.800                     | 2.000 | 0.071                | 0.079 |
| L        | 0.550 REF                 |       | 0.022 REF            |       |
| L1       | 0.300                     | 0.500 | 0.012                | 0.020 |
| $\theta$ | 0°                        | 8°    | 0°                   | 8°    |

## SOT-23 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05$  mm.
  3. The pad layout is for reference purposes only.

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